

MNLMH6628-X-RH REV 0A0

MICROCIRCUIT DATA SHEET

Original Creation Date: 04/29/03 Last Update Date: 05/13/03

Last Major Revision Date:

DUAL WIDEBAND, LOW-NOISE, VOLTAGE FEEDBACK OP AMP, GUARANTEED TO 300k rd(Si) TESTED TO MIL-STD-883, METHOD 1019

General Description

The National LMH6628 is a high speed dual op amp that offers a traditional voltage feedback topology featuring unity-gain stability and slew-enhanced circuitry. The LMH6628's low noise and very low harmonic distortion combine to form a very wide dynamic range op amp that operates from a single (5 to 12V) or dual $(\pm 5\text{V})$ power supply.

Each of the LMH6628's closely matched channels provides a 300MHz unity gain bandwidth and low input voltage noise density (2nV/SqRtHz). Low 2nd/3rd harmonic distortion (-65/-74dBc at 10MHz) makes the LMH6628 a perfect wide dynamic-range amplifier for matched I/Q

With its fast and accurate settling (12ns to 0.1%), the LMH6628 is also an excellent choice for wide dynamic range, anti-aliasing filters to buffer the inputs of hi resolution analog-to-digital converters. Combining the LMH6628's two tightly matched amplifiers in a single package reduces cost and board space for many composite amplifier applications such as active filters, differential line drivers/receivers, fast peak detectors and instrumentation amplifiers.

The LMH6628 is fabricated using National's VIP 10 (TM) comlimentary bipolar process.

Industry Part Number

LMH6628

Prime Die

LMH6628A

Controlling Document

SEE FEATURES SECTION

NS Part Numbers

LMH6628J-QML LMH6628J-QMLV LMH6628JFQML LMH6628JFQMLV LMH6628WG-QML LMH6628WG-QMLV LMH6628WGFQMLV LMH6628WGFQMLV

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Processing

MIL-STD-883, Method 5004

Quality Conformance Inspection

MIL-STD-883, Method 5005

Subgrp Description Temp (°C)

+25

2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

Static tests at

Features

- Wide unity-gain bandwidth: 300 MHz

- Low noise: 2.0nV/SqRtHz

- Low distortion: -65/-74dBc (10MHz)

- Settling time: 12ns to 0.1%

- Wide supply voltage range: $\pm 2.5 \text{V}$ to $\pm 6 \text{V}$

- High output current $\pm 85 \text{mA}$

- Improved replacement for CLC428

CONTROLLING DOCUMENTS:

LMH6628J-QML 5962-0254501MPA
LMH6628J-QMLV 5962-0254501VPA
LMH6628JFQML 5962F0254501MPA
LMH6628JFQMLV 5962F0254501VPA
LMH6628WG-QML 5962-0254501MZA
LMH6628WGFQMLV 5962-0254501VZA
LMH6628WGFQML 5962F0254501MZA
LMH6628WGFQML 5962F0254501MZA

Applications

- High speed dual op amp
- Low noise integrators
- Low noise active filters
- Driver/receiver for transmission systems
- High-speed detectors
- I/Q channel amplifiers

(Absolute Maximum Ratings)

(Note 1)

Supply Voltage <u>+</u>7V dc Maximum Junction temperature (Note 2) +175 C Lead temperature Soldering, 10 seconds +300 C Differential input voltage V+ - V-Common mode input voltage V+ - V-Storage temperature range -65 C \leq Ta \leq +150 C Power Dissipation (Note 2) 1.0W Short circuit current (Note 3) Thermal Resistance ThetaJA Ceramic DIP (Still Air) 135 C/W (500LF/Min Air Flow) 75 C/W Ceramic SOIC (Still Air) 200 C/W (500LF/Min Air Flow) 145 C/W ThetaJC Ceramic DIP 30 C/W Ceramic SOIC 19 C/W Package Weight (typical) Ceramic DIP TBD Ceramic SOIC TBD ESD Tolerance (Note 4) 4000V

- Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.
- The maximum power dissipation must be derated at elevated temperatures and is dictated by Tjmax (maximum junction temperature), ThetaJA (package junction to ambient thermal resistance), and TA (ambient temperatuer). The maximum allowable power dissipation at any temperatuer is Pdmax = (Tjmax -TA) / ThetaJA or the number Note 2: given in the Absoulute Maximum Ratings, whichever is lower.
- Note 3: Output is short circuit protected to ground, however maximum reliability is obtained if output current does not exceed 160mA. Human body model, 1.5k Ohms in series with 100pF.
- Note 4:

Recommended Operating Conditions

Supply Voltage

 ± 2.5 V to ± 6.0 V

Ambient Operating Temperture Range

-55 C ≤ Ta ≤ +125 C

Electrical Characteristics

DC PARAMETERS: Static and DC Tests

(The following conditions apply to all the following parameters, unless otherwise specified.) DC: Vcc = ± 5 V dc, Av = +2, Rl = 100 Ohms, Rf = 100 Ohms, -55 C \leq Ta \leq +125 C

SYMBOL	PARAMETER CONDITIONS		NOTES PIN-		MIN	MAX	UNIT	SUB- GROUPS	
Ib	Input Bias Current		3		-10	+10	uA	1	
	Gullens				-20	+20	uA	2	
					-20	+20	uA	3	
Vio	Input Offset Voltage		3		-2	+2	mV	1	
	Voicage				-2.6	+2.6	mV	2, 3	
Icc	Supply Current	Rl = infinity	3			24	mA	1	
						24	mA	2	
						25	mA	3	
PSRR	Power Supply Rejection Ration	+Vs = +4.0V to $+5.0v$, $-Vs = -4.0V$ to $-5.0V$			60		dB	1	
	Rejection Ration	3.00			55		dB	2, 3	
Vout	Output Voltage Range	Rl = Infinity			-5.0	+5.0	V	1, 2,	

AC PARAMETERS: Frequeuncy Domain Response

(The following conditions apply to all the following parameters, unless otherwise specified.) AC: Vcc = ± 5 V dc, Av = +2, Rl = 100 Ohms, Rf = 100 Ohms, -55 C \leq Ta \leq +125 C

SSBW	Small Signal -3 dB bandwidth, Vout < 0.5 Vpp Bandwith		2	50		MHz	4
GFP	Gain Flatness Peaking 0.1 MHz to 200 MHz, Vout ≤0.5 Vpp		2		0.6	dB	4
GFR	Gain Flatness Rolloff 0.1 MHz to 20 MHz, Vout ≤0.5 Vpp		2		0.6	dВ	4
Aol	Open Loop Gain		2	55		dВ	4

AC PARAMETERS: Distortion and Noise Tests.

(The following conditions apply to all the following parameters, unless otherwise specified.) AC: Vcc = \pm 5V dc, Av = +2, Rl = 100 Ohms, Rf = 100 Ohms, -55 C \leq Ta \leq +125 C

HD2	Second Harmonic Distortion	1 Vpp at 10 MHz	2		50	dBc	4
HD3	Third Harmonic Distortion	1 Vpp at 10 MHz	2		60	dBc	4

Electrical Characteristics

DC PARAMETERS: DRIFT VALUES

(The following conditions apply to all the following parameters, unless otherwise specified.)

DC: "Deltas not required on B-Level product. Deltas required for S-Level product at Group B5 ONLY, or as specified on the Internal Processing Instructions (IPI).

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Ib	Input Bias Current		1		-1.0	+1.0	uA	1
Vio	Input Offset Voltage		1		-0.2	+0.2	mV	1
Icc	Supply Current	Rl = Infinity	1		-1	+1	mA	1

If not tested, shall be guaranteed to the limits specified in table 1. Note 1:

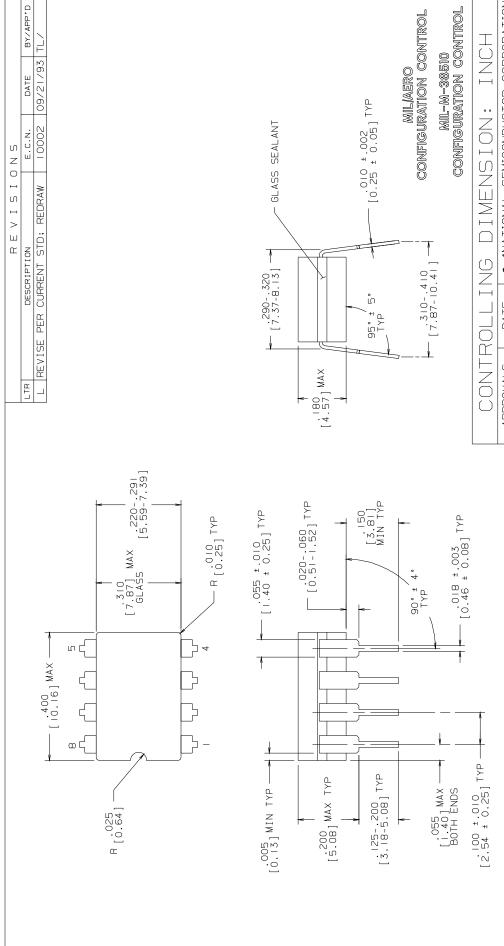
Note 2: Note 3: Group A testing only.

the and post irradiation limits are identical to those listed under electrical characteristics. These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, Method 1019. Pre and post irradiation limits are identical to those listed under electrical

Graphics and Diagrams

GRAPHICS#	DESCRIPTION
06403HRA1	CERAMIC SOIC (WG), 10 LEAD (B/I CKT)
07082HRA4	CERDIP (J), 8 LEAD (B/I CKT)
J08ARL	CERDIP (J), 8 LEAD (P/P DWG)
P000480A	CERDIP (J), 8 LEAD (PIN OUT)
P000484A	CERAMIC SOIC (WG), 10 LEAD (PIN OUT)
WG10ARC	CERAMIC SOIC (WG), 10 LEAD (P/P DWG)

See attached graphics following this page.



NATIONAL SEMICONDUCTOR CORPORATION 2900 Semiconductor Drive, Santa Clara, CA 95052-8090 MKT-J08A CERDIP (, 8 LEAD \forall | DRAWN_T. LEQUANG | 09/21/93 DATE PROJECTION APPROVALS DFTG. CHK. ENGR. CHK. APPROVAL

> 1. LEAD FINISH TO BE 200 MICROINCHES / 5.08 MICROMETERS MINIMUM SOLDER MEASURED AT THE CREST OF THE MAJOR FLATS. 2. JEDEC REGISTRATION MO-036, VARIATION AA, DATED 04/1981.

NOTES: UNLESS OTHERWISE SPECIFIED

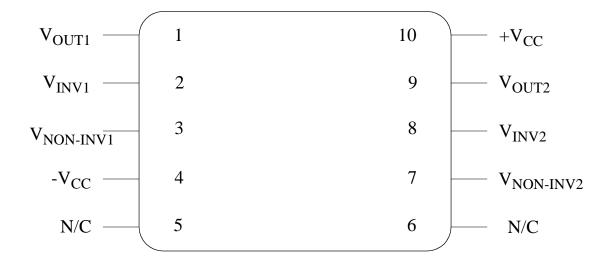
R V

DO NOT SCALE DRAWING SHEET



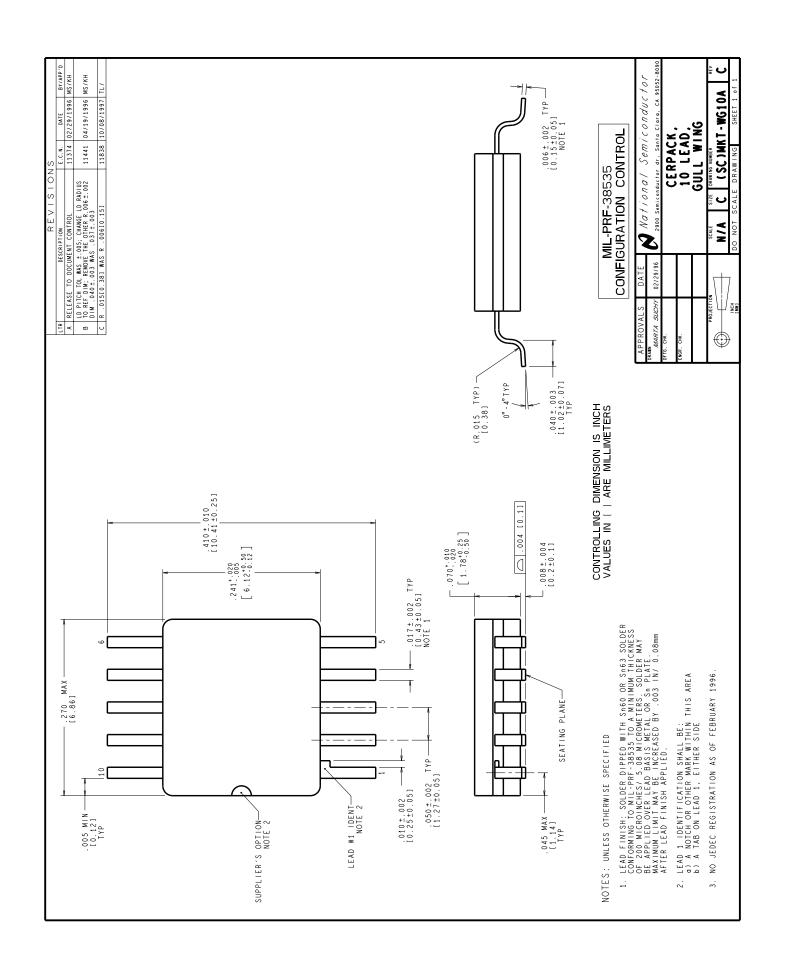
LMH6628J 8 - LEAD DIP CONNECTION DIAGRAM TOP VIEW P000480A





LMH6628WG 10 - LEAD CERAMIC SOIC CONNECTION DIAGRAM TOP VIEW P000484A





Revision History

Rev	ECN #	Rel Date	Originator	Changes
0A0	M0004149	05/13/03	Rose Malone	Initial MDS Release: MNLMH6628-X-RH, Rev. 0A0